

N-Channel Enhancement Mode Field Effect Transistor

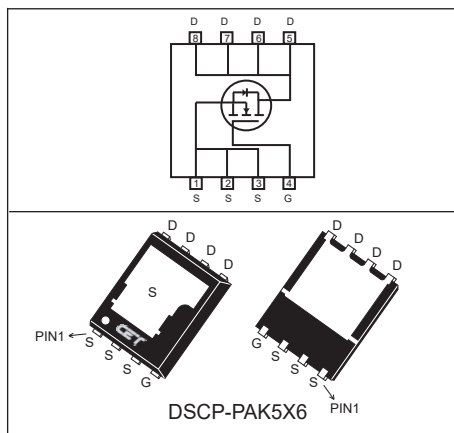
FEATURES

- High power and current handling capability.
- Reliable and rugged.
- Pb-free lead plating ; RoHS compliant.
- Halogen Free.
- Surface mount Package.

APPLICATIONS

- Synchronous rectification.
- DC/DC converter.
- Battery protection charge.
- Load switch.

V_{DS}	$R_{DS(ON)}$ typ @ V_{GS}	I_D
60V	$1.1m\Omega @ V_{GS} = 10V$	235A



ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ C$ unless otherwise noted

Parameter		Symbol	Limit	Units
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	± 20	V
Drain Current-Continuous	$I_D @ R_{\theta JC}$	$T_C = 25^\circ C$	235	A
		$T_C = 100^\circ C$	166	A
	$I_D @ R_{\theta JA}$	$T_A = 25^\circ C$	53	A
		$T_A = 100^\circ C$	37	A
Drain Current-Pulsed ^a	$I_{DM} @ R_{\theta JC}$	$T_C = 25^\circ C$	940	A
	$I_{DM} @ R_{\theta JA}$	$T_A = 25^\circ C$	212	A
Maximum Power Dissipation		P_D	147	W
Single Pulsed Avalanche Energy ^d		E_{AS}	320	mJ
Single Pulsed Avalanche Current ^d		I_{AS}	80	A
Operating and Store Temperature Range		T_J, T_{stg}	-55 to 175	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Limit	Units
Thermal Resistance, Junction-to-Case bottom	$R_{\theta JC}$	1.2	$^\circ C/W$
Thermal Resistance, Junction-to-Case top	$R_{\theta JC}$	1.02	$^\circ C/W$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	20	$^\circ C/W$

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60V, V_{GS} = 0V$			1	μA
Gate Body Leakage Current, Forward	I_{GSSF}	$V_{GS} = 20V, V_{DS} = 0V$			100	nA
Gate Body Leakage Current, Reverse	I_{GSSR}	$V_{GS} = -20V, V_{DS} = 0V$			-100	nA
On Characteristics ^b						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	2.4	3.0	3.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 20A$		1.1	1.4	m Ω
Gate input resistance	R_g	f=1MHz,open Drain		2.2		Ω
Dynamic Characteristics ^c						
Input Capacitance	C_{iss}	$V_{DS} = 30V, V_{GS} = 0V,$ $f = 1.0\text{ MHz}$		5100		pF
Output Capacitance	C_{oss}			1935		pF
Reverse Transfer Capacitance	C_{rss}			90		pF
Switching Characteristics ^c						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 30V, I_D = 15A,$ $V_{GS} = 10V, R_{GEN} = 3\Omega$		31		ns
Turn-On Rise Time	t_r			14		ns
Turn-Off Delay Time	$t_{d(off)}$			65		ns
Turn-Off Fall Time	t_f			17		ns
Total Gate Charge	Q_g	$V_{DS} = 30V, I_D = 15A,$ $V_{GS} = 10V$		80		nC
Gate-Source Charge	Q_{gs}			17		nC
Gate-Drain Charge	Q_{gd}			21		nC
Drain-Source Diode Characteristics and Maximun Ratings						
Drain-Source Diode Current-Continuous	I_S				173	A
Drain-Source Diode Current-Pulsed ^b	I_{SM}				940	A
Drain-Source Diode Forward Voltage ^b	V_{SD}	$V_{GS} = 0V, I_S = 2A$			1.2	V
Notes :						
a.Repetitive Rating : Pulse width limited by maximum junction temperature.						
b.Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.						
c.Guaranteed by design, not subject to production testing.						
d.L = 0.1mH, $I_{AS} = 80A, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^\circ C$.						

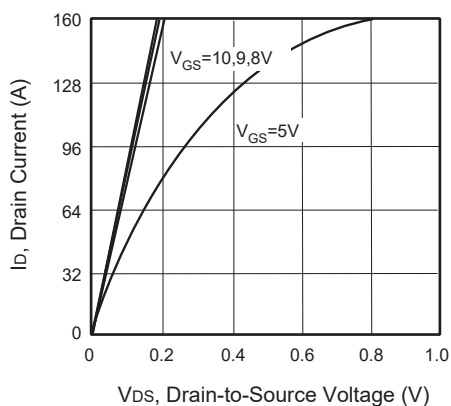


Figure 1. Output Characteristics

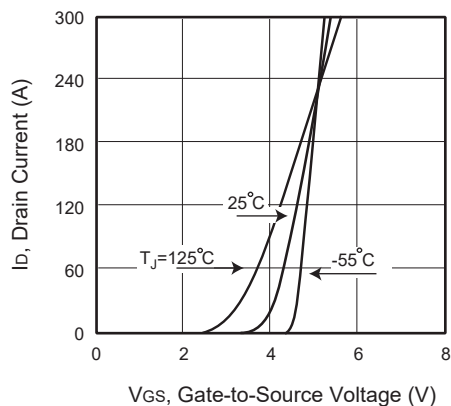


Figure 2. Transfer Characteristics

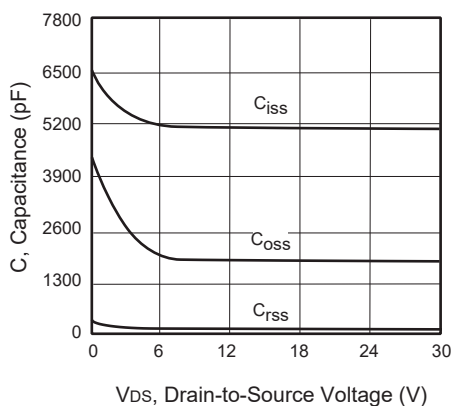


Figure 3. Capacitance

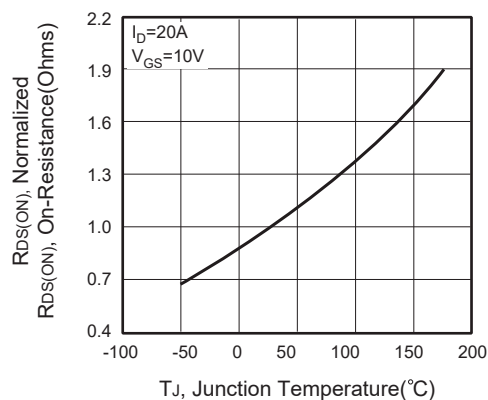


Figure 4. On-Resistance Variation with Temperature

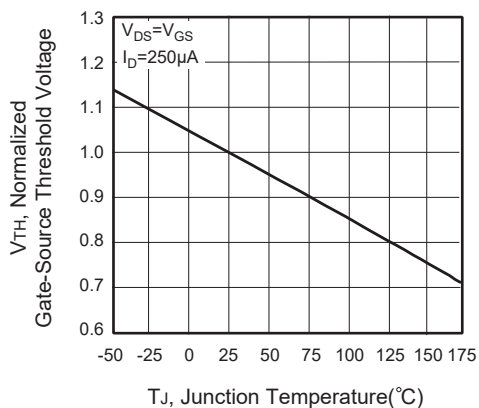


Figure 5. Gate Threshold Variation with Temperature

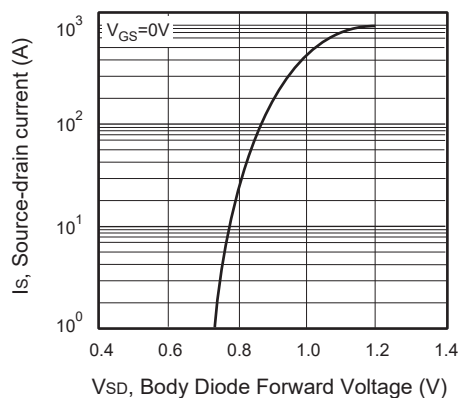


Figure 6. Body Diode Forward Voltage Variation with Source Current

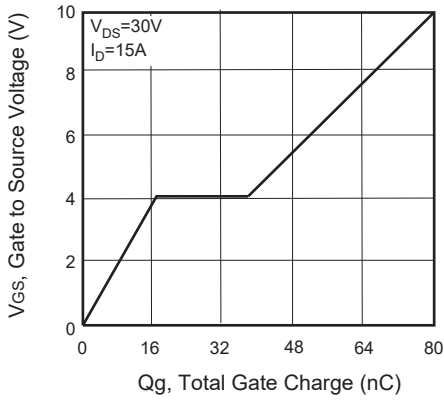


Figure 7. Gate Charge

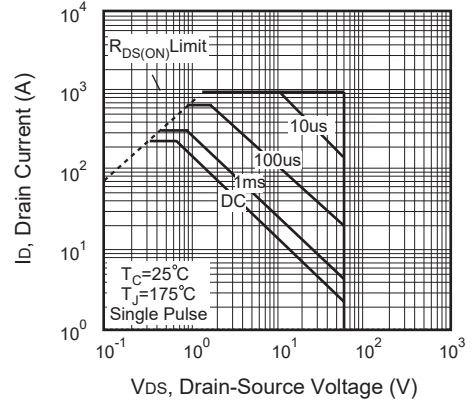


Figure 8. Maximum Safe Operating Area

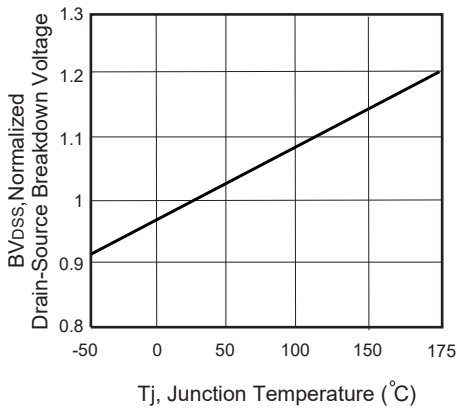


Figure 9. Breakdown Voltage Variation VS Temperature

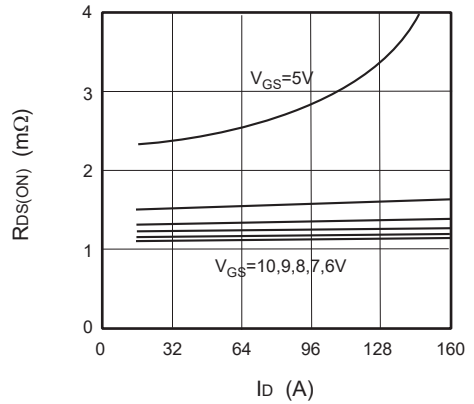


Figure 10. On-Resistance VS Drain Current

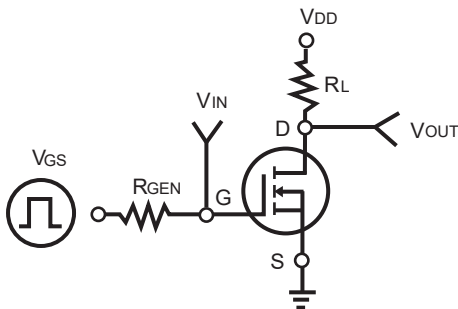


Figure 11. Switching Test Circuit

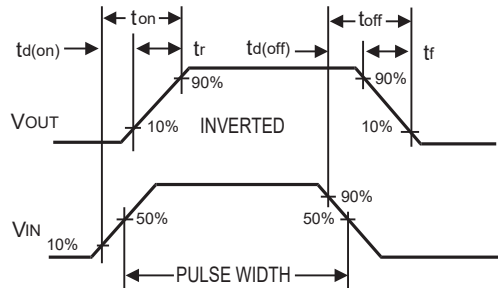


Figure 12. Switching Waveforms

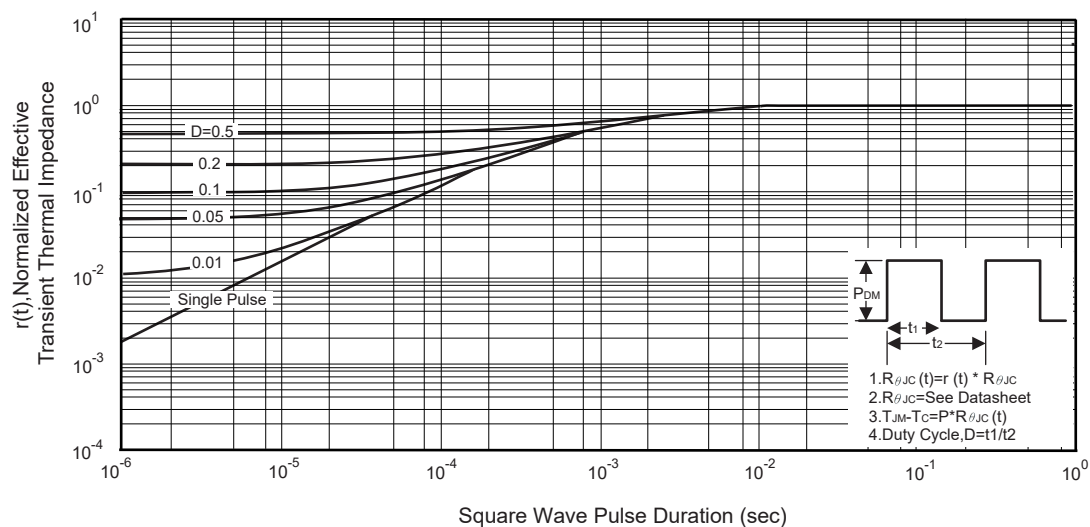
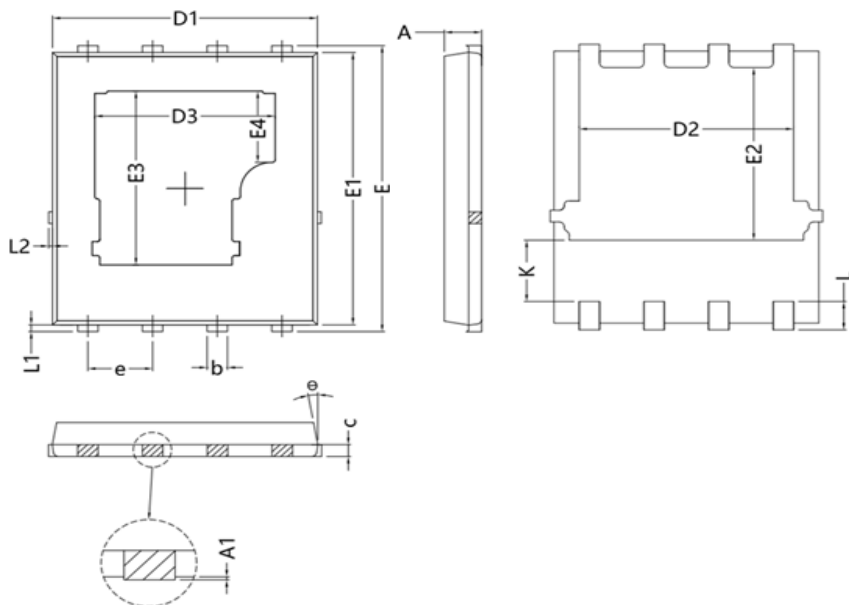


Figure 13. Normalized Thermal Transient Impedance Curve

DSCP-PAK5X6 產品外觀尺寸圖 (Product Outline Dimension)



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.600	0.830	0.024	0.033
A1	0.000	0.050	0.000	0.002
b	0.300	0.500	0.012	0.020
c	0.200	0.300	0.008	0.012
D1	5.100	5.300	0.201	0.209
D2	4.060	4.360	0.160	0.172
D3	3.390	3.690	0.133	0.145
E	6.000	6.300	0.236	0.248
E1	5.760	5.960	0.227	0.235
E2	3.570	3.870	0.141	0.152
E3	3.588	3.888	0.141	0.153
E4	1.382	1.682	0.054	0.066
e	1.270BSC		0.050BSC	
L	0.500	0.710	0.020	0.028
L1	0.050	0.250	0.002	0.010
L2	0.020	0.150	0.001	0.006
K	1.100	~	0.043	~
θ	8°	12°	8°	12°